RoHS COMPLIANT

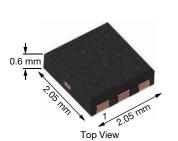
HALOGEN

FREE

www.vishay.com Vishay Siliconix

P-Channel 20 V (D-S) MOSFET

Thin PowerPAK® SC-70-6L Single





Bottom View

Marking code: BP

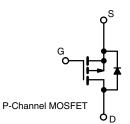
PRODUCT SUMMARY	
V _{DS} (V)	-20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0205
$R_{DS(on)}$ max. (Ω) at V_{GS} = -2.5 V	0.0270
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8 \text{ V}$	0.0360
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5 \text{ V}$	0.0600
Q _g typ. (nC)	24.5
I _D (A) ^a	-12
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- New thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Ultra-thin 0.6 mm height
 - Low on-resistance
- 100 % R_a tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Load switch and charger switch for portable devices
- DC/DC converter



ORDERING INFORMATION							
Package	Thin PowerPAK SC-70						
Lead (Pb)-free and halogen-free	SiA429DJT-T1-GE3						

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unless	s otherwise note	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-20	V
Gate-source voltage		V_{GS}	± 8	v
	T _C = 25 °C		-12 ^a	
Continuous drain augrent (T. 150 °C)	T _C = 70 °C		-12 ^a	
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	l _D	-10.6 ^{b, c}	
	T _A = 70 °C		-8.5 ^{b, c}	Α
Pulsed drain current (t = 300 μs)		I _{DM}	-30	
Continuous source drain diada surrent	T _C = 25 °C		-12 ^a	
Continuous source-drain diode current	T _A = 25 °C	I _S	-2.9 ^{b, c}	
	T _C = 25 °C		19	
Mandan and a super discipation	T _C = 70 °C		12	14/
Maximum power dissipation	T _A = 25 °C	P _D	3.5 b, c	w
	T _A = 70 °C		2.2 ^{b, c}	
Operating junction and storage temperature rai	nge	T _J , T _{stg}	-55 to +150	00
Soldering recommendations (peak temperature	e) d, e		260	°C

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R_{thJA}	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	5.3	6.5	C/W				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components f. Maximum under steady state conditions is 80 °C/M
- Maximum under steady state conditions is 80 °C/W

Vishay Siliconix

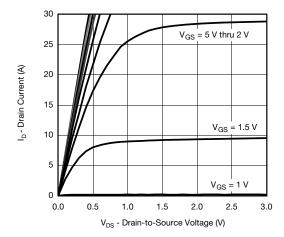
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT			
Static				•					
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	-	-	V			
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	-12	-	mV/°C			
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	2.7	-				
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-	-1	V			
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 100	nA			
Zana a da calla da		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μΑ			
Zero gate voltage drain current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10				
On-state drain current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-20	-	-	Α			
		$V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A}$	-	0.0170	0.0205				
Duning and the seriet and 3		$V_{GS} = -2.5 \text{ V}, I_D = -2 \text{ A}$	-	0.0220	0.0270	0			
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -1.8 \text{ V}, I_D = -2 \text{ A}$	-	0.0290	0.0360	Ω			
		V _{GS} = -1.5 V, I _D = -1 A	-	0.0380	0.0600	1			
Forward transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_{D} = -6 \text{ A}$	-	30	-	S			
Dynamic ^b									
Input capacitance	C _{iss}		-	1750	-				
Output capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	270	-	pF			
Reverse transfer capacitance	C _{rss}		-	240	-				
+		V _{DS} = -10 V, V _{GS} = -8 V, I _D = -10 A	-	41	62	nC			
Total gate charge	Q_g Q_{gs}		-	24.5	37				
Gate-source charge		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -10 \text{ A}$	-	2.4	-				
Gate-drain charge	Q _{qd}		-	6.7	-				
Gate resistance	R_{q} $f = 1 \text{ MHz}$		1.3	6.3	13	Ω			
Turn-on delay time	t _{d(on)}		-	22	35				
Rise time	t _r	V_{DD} = -10 V, R_L = 1.2 Ω	-	25	40	ns			
Turn-off delay time	t _{d(off)}	$I_D \cong -8.5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	70	105				
Fall time	t _f		-	25	40				
Turn-on delay time	t _{d(on)}		-	10	15				
Rise time	t _r	$V_{DD} = -10 \text{ V}, R_L = 1.2 \Omega$		10	15				
Turn-off delay time	t _{d(off)}	$I_D \cong -8.5 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	80	120				
Fall time	-4(01)					•			
Drain-Source Body Diode Characterist	ics								
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	-12				
Pulse diode forward current	I _{SM}		-	-	-30	A			
Body diode voltage	V_{SD}	I _S = -8.5 A, V _{GS} = 0 V	-	-0.8	-1.2	V			
Body diode reverse recovery time	t _{rr}		-	35	60	ns			
Body diode reverse recovery charge	Q _{rr}	$I_F = -8.5 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	18	30	nC			
Reverse recovery fall time	t _a	$T_J = 25 ^{\circ}\text{C}$	-	13	-				
Reverse recovery rise time	t _b		-	22	_	ns			

Notes

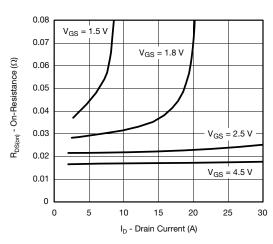
- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

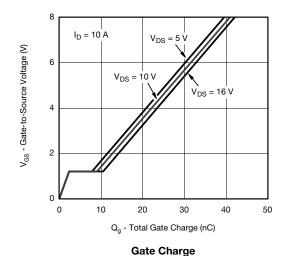


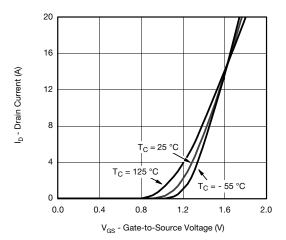


Output Characteristics

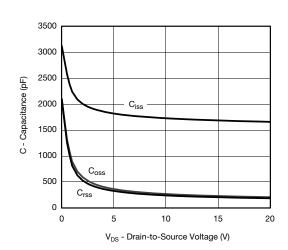


On-Resistance vs. Drain Current and Gate Voltage

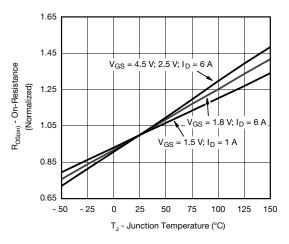




Transfer Characteristics

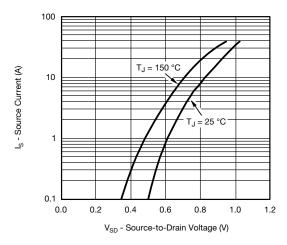


Capacitance

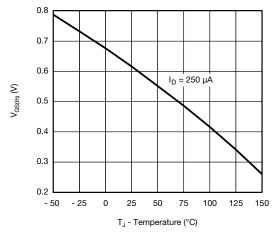


On-Resistance vs. Junction Temperature

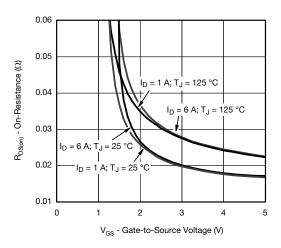




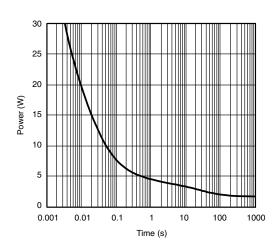
Source-Drain Diode Forward Voltage



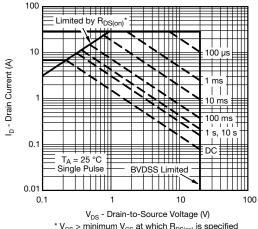
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



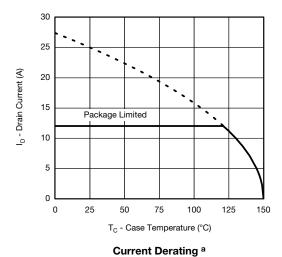
Single Pulse Power, Junction-to-Ambient

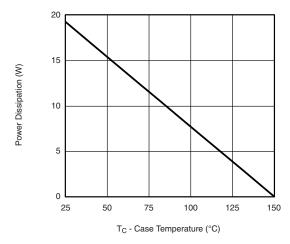


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient





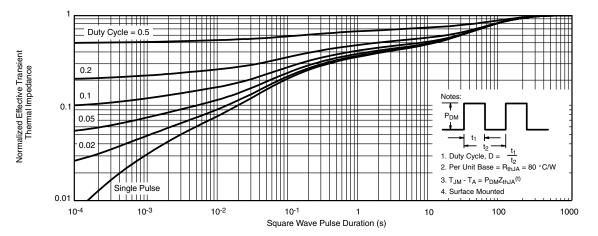


Power Derating

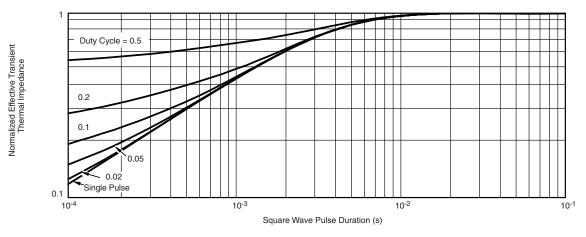
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

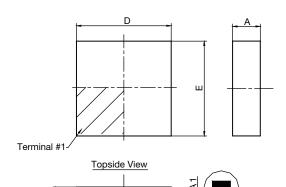


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for silicon technology and package reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67038.

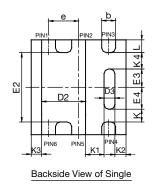


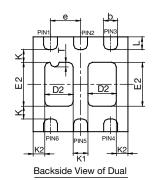




Side View

Detail Z





	SINGLE PAD						DUAL PAD						
DIM.	MILLIMETERS INCHES		N	MILLIMETERS			INCHES						
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.525	0.60	0.65	0.0206	0.024	0.026	0.525	0.60	0.65	0.0206	0.024	0.026	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D2	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D3	0.135	0.235	0.335	0.005	0.009	0.013							
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E2	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E3	0.345	0.395	0.445	0.014	0.016	0.018							
E4	0.425	0.475	0.525	0.017	0.019	0.021						i	
е		0.65 BSC			0.026 BSC	;		0.65 BSC			0.026 BSC		
K		0.275 TYP.			0.011 TYP.		0.275 TYP.			0.011 TYP.			
K1		0.400 TYP.			0.016 TYP.	•	0.320 TYP.			0.013 TYP.			
K2		0.240 TYP.			0.009 TYP.			0.252 TYP.			0.010 TYP.		
K3		0.225 TYP.		0.009 TYP.									
K4		0.355 TYP.		0.014 TYP.									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
T							0.05	0.10	0.15	0.002	0.004	0.006	
ECN: C12-0160-Rev. B, 05-Mar-12 DWG: 5994													

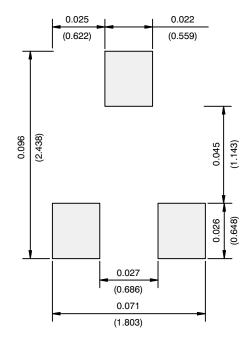
Case Outline for PowerPAK® SC70T

Notes

- 1. All dimensions are in millimeter. Millimeters will govern.
- 2. Package outline exculsive of mold flash and metal burr.
- 3. Package outline inclusive of plating



RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



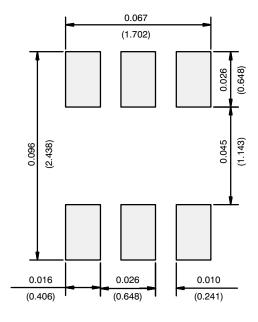
Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.